



STD40NF06LZ

N-CHANNEL 60V - 0.020 Ω - 40A DPAK Zener-Protected STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD40NF06LZ	60 V	< 25 m Ω	40 A

- TYPICAL R_{DS(on)} = 0.020 Ω
- 100% AVALANCHE TESTED
- LOW GATE CHARGE
- LOGIC LEVEL GATE DRIVE
- SURFACE-MOUNTING DPAK (TO-252)
POWER PACKAGE IN TAPE & REEL
(SUFFIX "T4")
- BUILT-IN ZENER DIODES TO IMPROVE ESD
PROTECTION UP TO 2kV

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

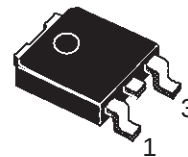
- SINGLE-ENDED SMPS IN MONITOTS,
COMPUTER AND INDUSTRIAL
APPLICATION
- WELDING EQUIPMENT
- AUTOMOTIVE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	60	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C	40	A
I _D	Drain Current (continuous) at T _C = 100°C	28	A
I _{DM} (•)	Drain Current (pulsed)	160	A
P _{tot}	Total Dissipation at T _C = 25°C	100	W
	Derating Factor	0.67	W/°C
V _{ESD(G-S)}	Gate-source ESD(HBM-C=100pF, R=15k Ω)	± 2.5	kV
dv/dt ⁽¹⁾	Peak Diode Recovery voltage slope	9	V/ns
E _{AS} ⁽²⁾	Single Pulse Avalanche Energy	450	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Max. Operating Junction Temperature		

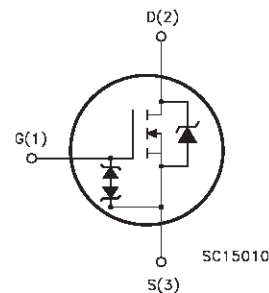
(•) Pulse width limited by safe operating area.

(1) I_{SD} $\leq$ 40A, di/dt $\leq$ 100A/ μ s, V_{DD} $\leq$ V_{(BR)DSS}, T_j $\leq$ T_{JMAX}.
(2) Starting T_j = 25 °C I_D = 20A V_{DD} = 45V



**DPAK
TO-252**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



STD40NF06LZ

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.5	°C/W
R _{thj-PCB}	Thermal Resistance Junction-PCB (#)	Max	50	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

(#) When Mounted on 1 inch² FR-4 board, 2 oz Cu.

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±10	μA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 5 V I _D = 20 A V _{GS} = 10 V I _D = 20 A			0.030 0.025	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 20 A		25		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1360 302 115		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		17 75		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48\text{ V}$ $I_D = 40\text{ A}$ $V_{GS} = 10\text{ V}$		54 11 12		nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 30\text{ V}$ $I_D = 20\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		38 23		ns ns

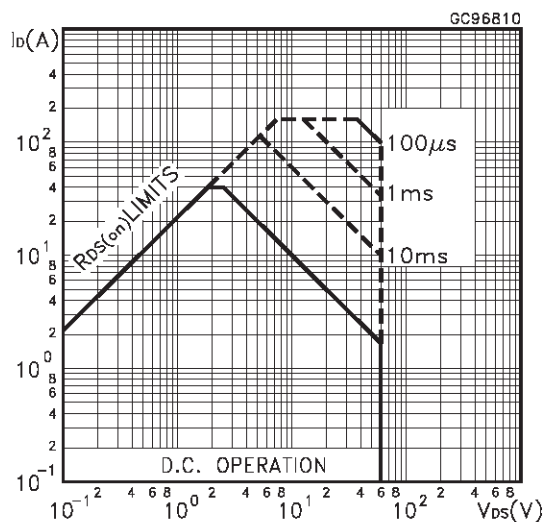
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				40 160	A A
$V_{SD}^(*)$	Forward On Voltage	$I_{SD} = 40\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 40\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		66 142 4.3		ns nC A

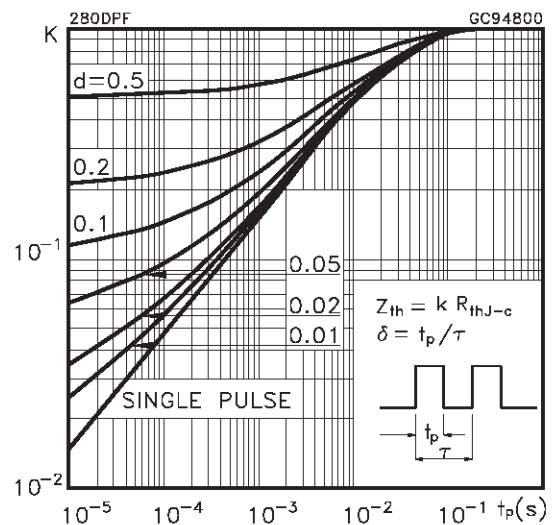
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(•) Pulse width limited by safe operating area.

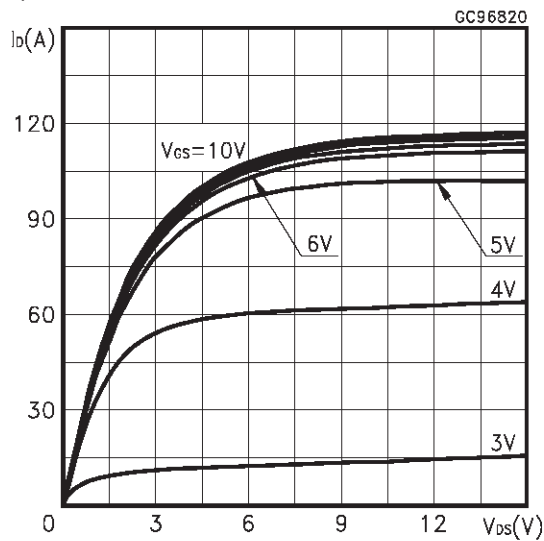
Safe Operating Area



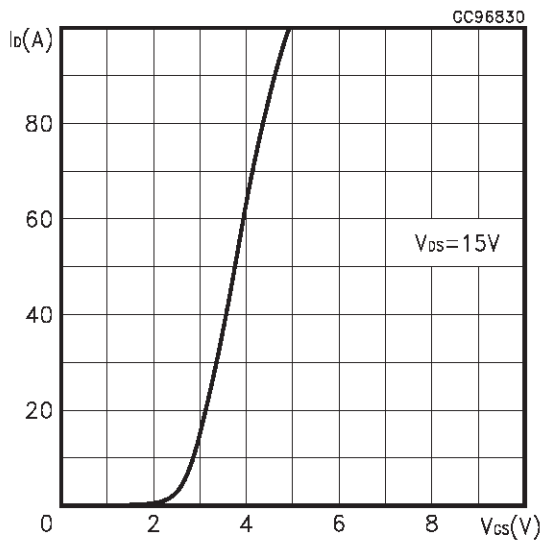
Thermal Impedance



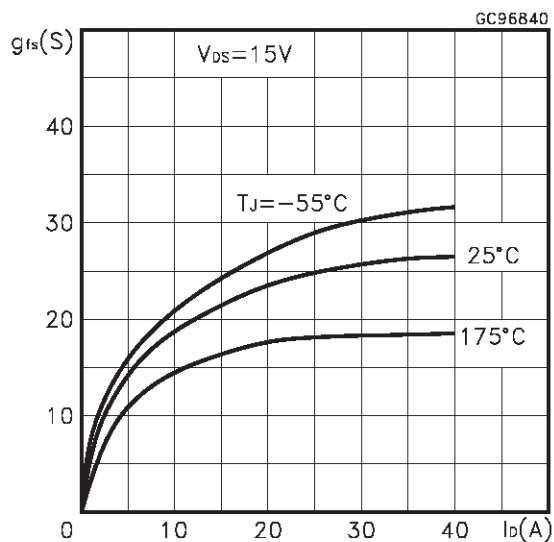
Output Characteristics



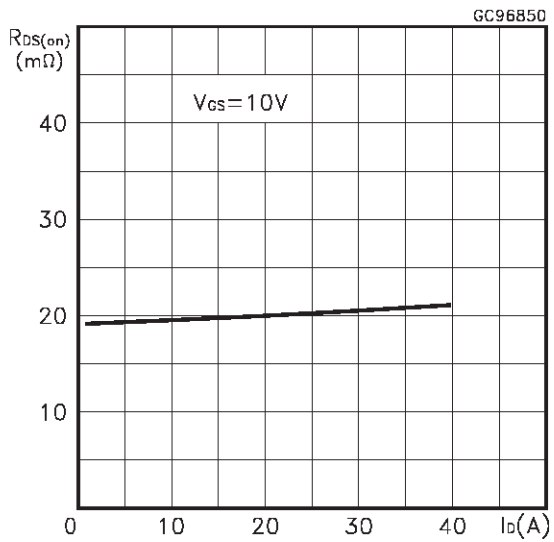
Transfer Characteristics



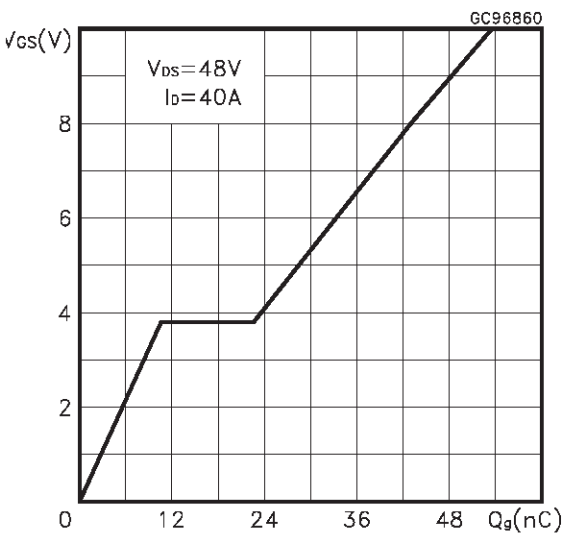
Transconductance



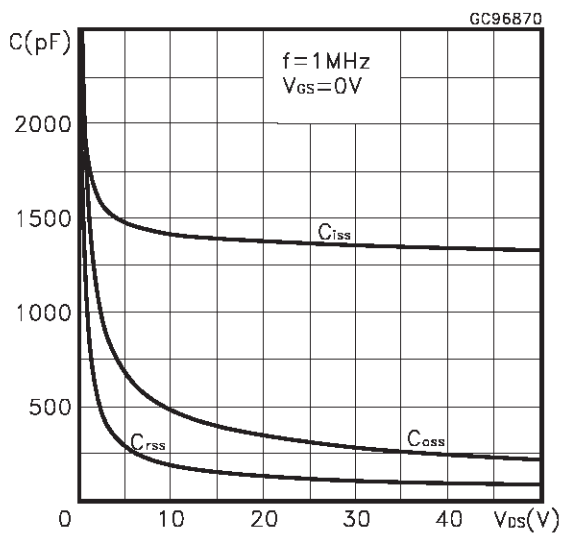
Static Drain-source On Resistance



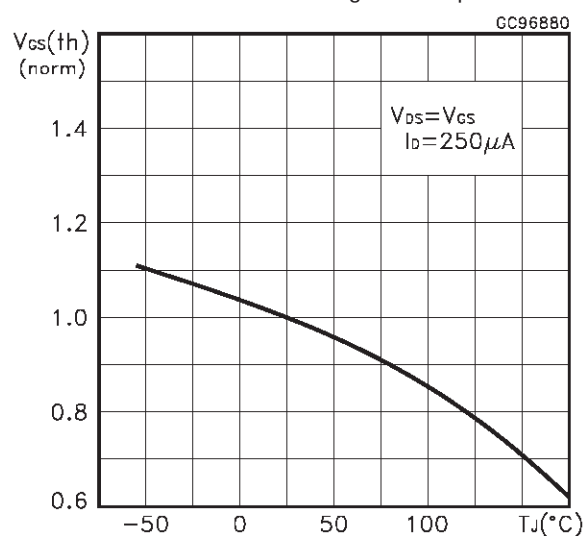
Gate Charge vs Gate-source Voltage



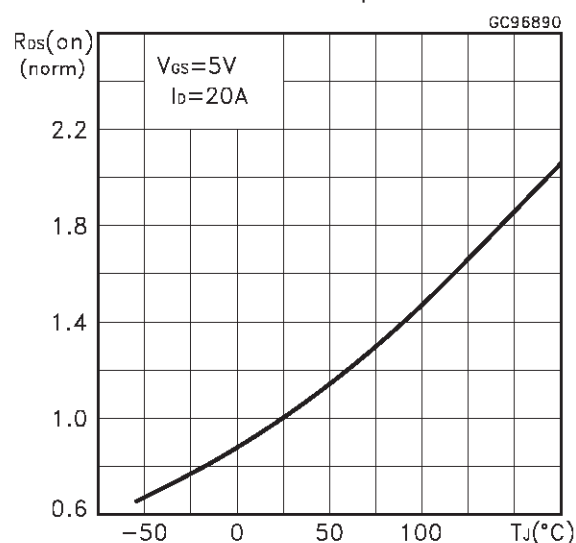
Capacitance Variations



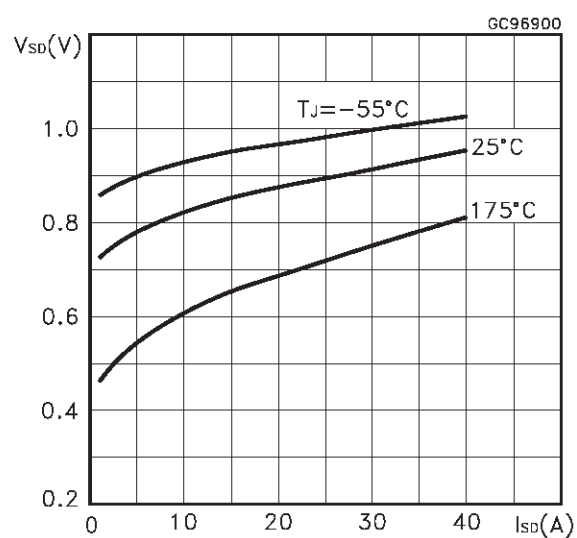
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

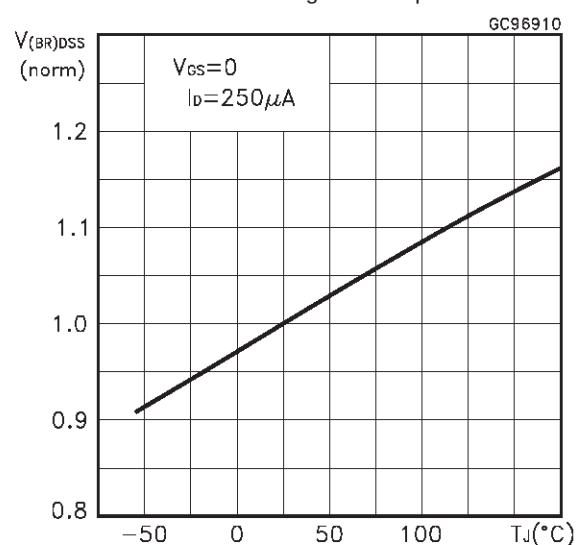


Fig. 1: Unclamped Inductive Load Test Circuit

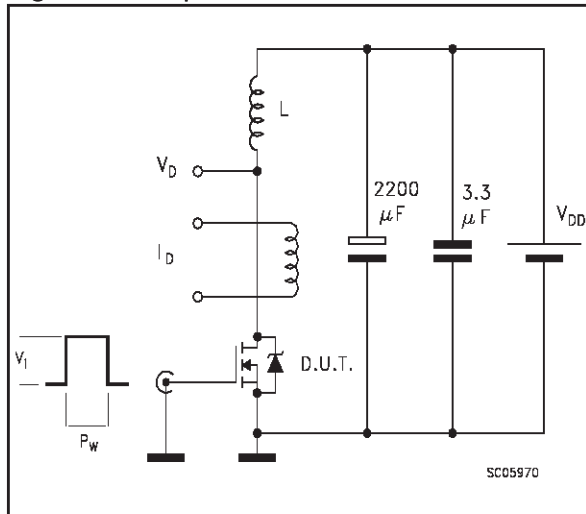


Fig. 2: Unclamped Inductive Waveform

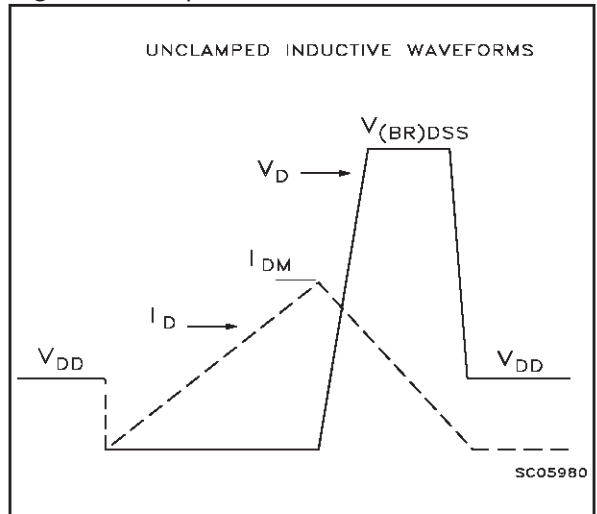


Fig. 3: Switching Times Test Circuits For Resistive Load

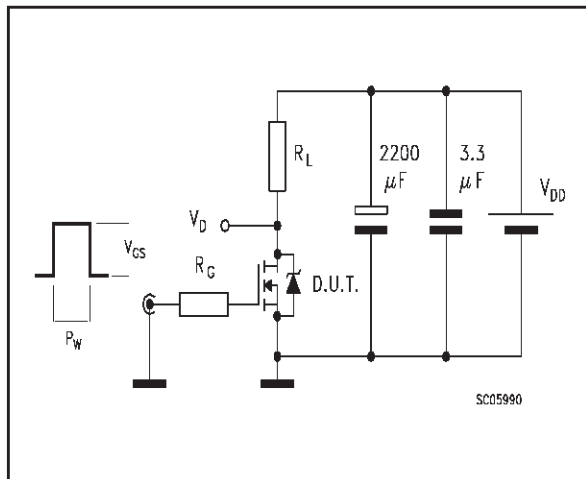


Fig. 4: Gate Charge test Circuit

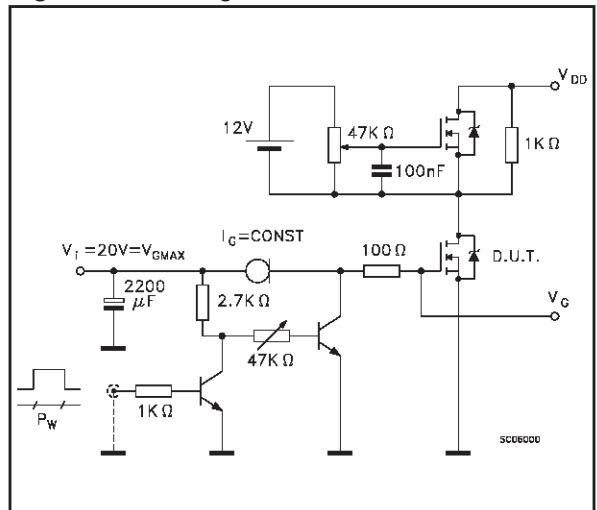
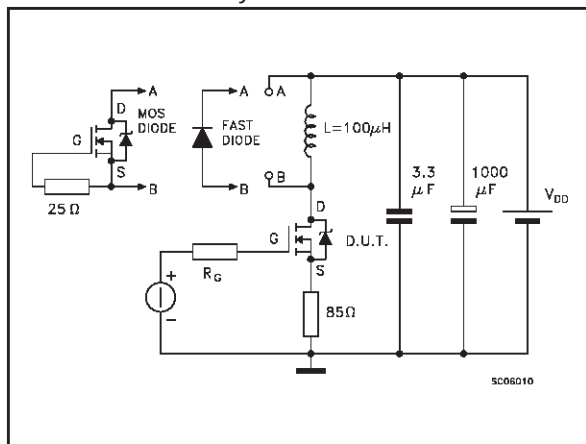
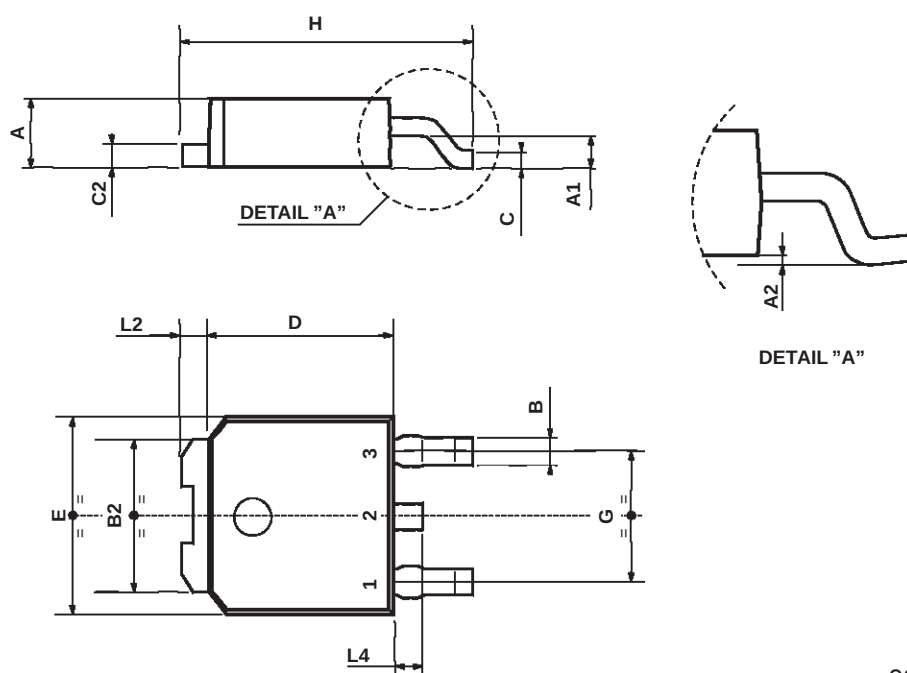


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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